

each have a vertex that is directed toward an inside of the second substrate, wherein each triangular bent portion circumvents a conductive contact dot; [and]
assembling the first substrate and the second substrate; and
forming a liquid crystal layer between the first and second substrates.

3. (Amended) The method according to claim 1, wherein the [seal pattern of the] triangular bent portions each include a first vertex, a second vertex, and a third vertex[es].

4. (Amended) The method according to claim 3, wherein the [seal pattern has a round with a radius in each of the vertexes] first vertex, the second vertex, and the third vertex all have a rounded shape that is defined by a radius.

5. (Amended) The method according to claim 4, wherein the radius [of the first, the second, and the third vertex] is 0.5 to 2 millimeters.

6. (Amended) The method according to claim 4, wherein a distance between [the] a first vertex and [the] a second vertex[es] is 5 to 20 millimeters.

7. (Amended) The method according to claim 4, wherein a distance between [the] a conductive contact dot and [the] a third vertex [of the triangular bent portion] is 0.1 to 5 millimeters.

8. (Amended) The method according to claim 1, wherein the seal pattern [forms] is formed by a dispenser.

9. (Amended) A method of forming [a seal pattern of] a liquid crystal display panel, comprising the steps of:

forming a common electrode on a first substrate;

forming a plurality of conductive contact dots on the second substrate;

forming a seal pattern [along edges of] on the second substrate, [said] the seal pattern having a plurality of semicircular bent portions, the semicircular bent portions being bent toward an inside of the second substrate wherein each semicircular bent portion circumvents a conductive contact dot; [and]

assembling the first substrate and the second substrate; and

forming a liquid crystal layer between first and second substrates.

11. (Amended) The method according to claim 9, wherein [a distance between the two ends of] the semicircular portion has a radius of 2.5 to 10 millimeters. [is 5 to 20 millimeters.]

12. (Amended) The method according to claim 9, wherein a distance between [the] a conductive contact dot and [the] a semicircular portion is 0.1 to 5 millimeters.